

ABSTRACT OF THE DISCLOSURE

NONVOLATILE SEMICONDUCTOR MEMORY DEVICE AND METHOD FOR MANUFACTURING SAME

Nonvolatile semiconductor memory device includes first memory cell array layer, first insulating layer formed thereabove, and second memory cell array layer formed thereabove. First memory cell array layer includes first NAND cell units each including plural first memory cells. The first memory cell includes first semiconductor layer, first gate insulating film formed thereabove, and first charge accumulation layer formed thereabove. The second memory cell array layer includes second NAND cell units each including plural second memory cells. The second memory cell includes second charge accumulation layer, second gate insulating film formed thereabove, and second semiconductor layer formed thereabove. Control gates are formed, via an inter-gate insulating film, on first-direction both sides of the first and second charge accumulation layers positioned the latter above the former via the first insulating layer. The control gates extend in a second direction perpendicular to the first direction.

FIG. 1

